## WHAT IS CLAIMED IS:

1. A method of forming a substantially haze-free BST film over a substrate assembly, comprising:

forming an electrode material over the substrate assembly;

forming a nucleation layer over the electrode material, wherein the nucleation layer is a metal; and

forming a BST film over the nucleation layer.

- 2. The method of Claim 1, wherein the nucleation layer is a member of the group consisting of Ti, Nb, and Mn.
  - 3. The method of Claim 1, wherein the electrode material is Pt.
- 4. The method of Claim 1, wherein the nucleation layer is formed to have a thickness of less than about 50 Å.
- 5. The method of Claim 1, wherein the BST film is deposited at a rate of between about 10 and about 100 Å/min.
- 6. The method of Claim 1, wherein the BST film is deposited at a rate of about 80 Å/min.
- 7. The method of Claim 1, wherein the BST film is formed such that it contains between about 50 and about 53.5 atomic percent Titanium.
- 8. The method of Claim 7, wherein the BST film is formed such that it contains about 52 to 53 atomic percent Titanium.
- 9. A method of forming a substantially haze-free BST film over a substrate assembly, comprising:

forming a first electrode material over the substrate assembly;

forming a nucleation layer over the first electrode material;

forming a BST film over the nucleation layer;

forming a second electrode material over the BST film;

wherein the nucleation layer is a metal selected from the group consisting of: Ti, Nb, and Mn.

10. The method of Claim 9, wherein the nucleation layer is formed directly over the first electrode material.

- 11. The method of Claim 9, wherein the resulting BST film comprises between about 50 and about 53.5 atomic percent titanium.
- 12. The method of Claim 9, wherein the resulting BST film comprises between about 52 and about 53 atomic percent titanium.
- 13. The method of Claim 9, wherein the BST film is between about 150 and about 300 Å thick.
- 14. The method of Claim 9, wherein the BST film is deposited at a rate of about 80 Å/min.
- 15. The method of Claim 9, further comprising raising the temperature of the substrate assembly to about 500 to 550 °C.